

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **SD1219** is Designed for 12.5 V Collector Modulated AM Class C Amplifier Service in the 118 to 136 MHz Avionics Communication Band.

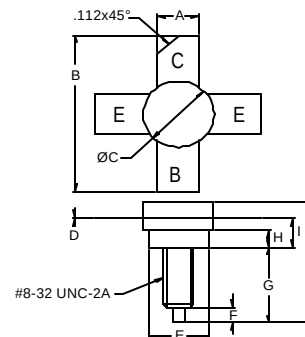
FEATURES:

- $P_G = 8$ dB Typical at 60 W/ 175 MHz
- Guaranteed 13.5 and 28 V Performance
- **OmniRel™** Metallization System

MAXIMUM RATINGS

I_C	6.5 A
V_{CE}	35 V
V_{CB}	65 V
P_{DISS}	75 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
q_{JC}	2.3°C/W

PACKAGE STYLE .380" 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10733

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 200$ mA		65			V
BV_{CEO}	$I_C = 200$ mA		35			V
BV_{EBO}	$I_E = 10$ mA		4.0			V
I_{CBO}	$V_{CB} = 30$ V				2.0	mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 500$ mA	5.0			---
C_{ob}	$V_{CB} = 30$ V	$f = 1.0$ MHz			80	pF
P_G	$V_{CE} = 28$ V	$P_{OUT} = 60$ W	7.0	8.0		dB
	$V_{CE} = 13.5$ V	$P_{OUT} = 17.5$ W	5.0	6.0		